

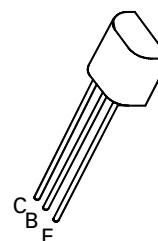
PNP SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

ZTX796A

ISSUE 1 – APRIL 94

FEATURES

- * 200 Volt V_{CEO}
- * Gain of 250 at $I_C=0.3$ Amps
- * Very low saturation voltage



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-200	V
Collector-Emitter Voltage	V_{CEO}	-200	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-0.5	A
Practical Power Dissipation*	P_{totp}	1.5	W
Power Dissipation at $T_{amb}=25^\circ\text{C}$ derate above 25°C	P_{tot}	1 5.7	W mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^\circ\text{C}$

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-200			V	$I_C=-100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-200			V	$I_C=-10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E=-100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-0.1	μA	$V_{CB}=-150\text{V}$
Emitter Cut-Off Current	I_{EBO}			-0.1	μA	$V_{EB}=-4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.2 -0.3 -0.3	V V V	$I_C=-50\text{mA}, I_B=-2\text{mA}^*$ $I_C=-100\text{mA}, I_B=-5\text{mA}^*$ $I_C=-200\text{mA}, I_B=-20\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-0.95	V	$I_C=-200\text{mA}, I_B=-20\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.67		V	$I_C=-200\text{mA}, V_{CE}=-10\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	300 300 250 100		800		$I_C=10\text{mA}, V_{CE}=-10\text{V}^*$ $I_C=100\text{mA}, V_{CE}=-10\text{V}^*$ $I_C=300\text{mA}, V_{CE}=-10\text{V}^*$ $I_C=400\text{mA}, V_{CE}=-10\text{V}^*$

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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$)

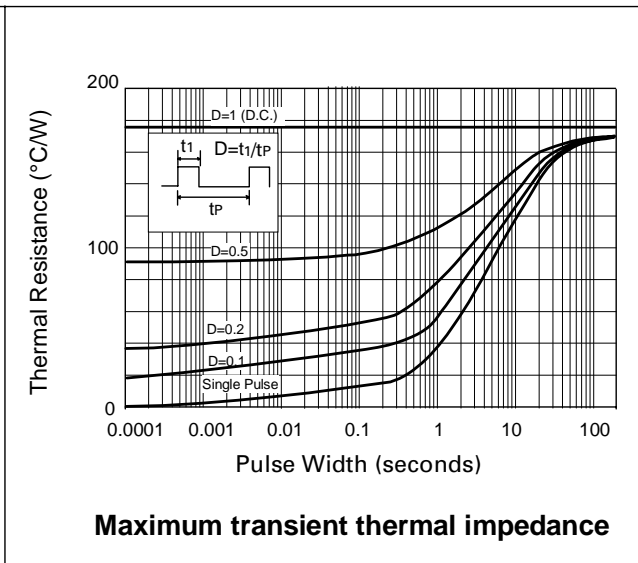
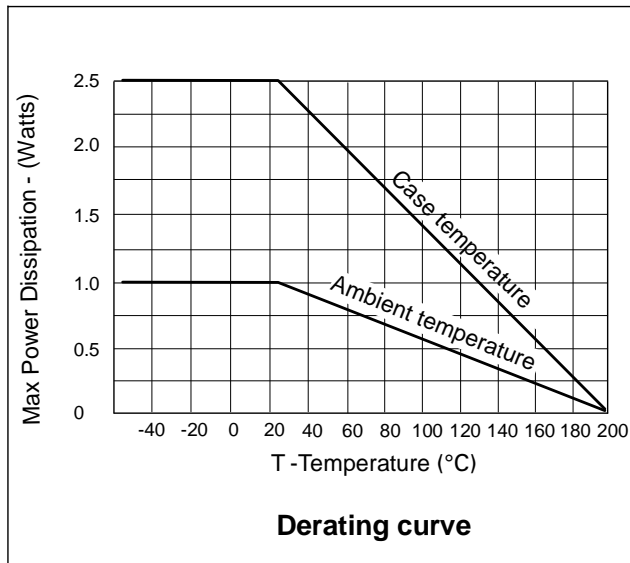
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Transition Frequency	f_T	100			MHz	$I_C = -50\text{mA}$, $V_{CE} = -5\text{V}$ $f = 50\text{MHz}$
Input Capacitance	C_{ibo}		225		pF	$V_{EB} = -0.5\text{V}$, $f = 1\text{MHz}$
Output Capacitance	C_{obo}		12		pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}$
Switching Times	t_{on} t_{off}		100 3200		ns ns	$I_C = -100\text{mA}$, $I_{B1} = -10\text{mA}$ $I_{B2} = -10\text{mA}$, $V_{CC} = -50\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient ₁	$R_{th(j-amb)1}$	175	$^{\circ}\text{C/W}$
Junction to Ambient ₂	$R_{th(j-amb)2}^{\dagger}$	116	$^{\circ}\text{C/W}$
Junction to Case	$R_{th(j-case)}$	70	$^{\circ}\text{C/W}$

\dagger Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.



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